### **MAXIMUM RATINGS**

Rating	Symbol	TIP100, TIP105	TIP101, TIP106	TIP102, TIP107	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	60	80	100	Vdc
Collector – Base Voltage	V <sub>CB</sub>	60	80	100	Vdc
Emitter – Base Voltage	V <sub>EB</sub>	5.0		Vdc	
Collector Current - Continuous - Peak	Ic	8.0 15			Adc
Base Current	I <sub>B</sub>		1.0		Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	80 0.64		W W/°C	
Unclamped Inductive Load Energy (1)	E	30		mJ	
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.0 0.016		W W/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-	-65 to +150	)	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	1.56	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1.  $I_C$  = 1.1 A, L = 50 mH, P.R.F. = 10 Hz,  $V_{CC}$  = 20 V,  $R_{BE}$  = 100  $\Omega$ 

### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS			ı	ı	
Collector-Emitter Sustaining Voltage (1)		V <sub>CEO(sus)</sub>			Vdc
$(I_C = 30 \text{ mAdc}, I_B = 0)$	TIP100, TIP105	()	60	_	
- '	TIP101, TIP106		80	_	
	TIP102, TIP107		100	-	
Collector Cutoff Current		I <sub>CEO</sub>			μAdc
$(V_{CE} = 30 \text{ Vdc}, I_B = 0)$	TIP100, TIP105		_	50	
$(V_{CE} = 40 \text{ Vdc}, I_B = 0)$	TIP101, TIP106		_	50	
$(V_{CE} = 50 \text{ Vdc}, I_B = 0)$	TIP102, TIP107		-	50	
Collector Cutoff Current		I <sub>CBO</sub>			μAdc
$(V_{CB} = 60 \text{ Vdc}, I_{E} = 0)$	TIP100, TIP105		_	50	
$(V_{CB} = 80 \text{ Vdc}, I_{E} = 0)$	TIP101, TIP106		_	50	
$(V_{CB} = 100 \text{ Vdc}, I_{E} = 0)$	TIP102, TIP107		-	50	
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	-	8.0	mAdc
ON CHARACTERISTICS (1)			•		•
DC Current Gain		h <sub>FE</sub>			_
$(I_C = 3.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$			1000	20,000	
$(I_C = 8.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$			200	-	
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>			Vdc
$(I_C = 3.0 \text{ Adc}, I_B = 6.0 \text{ mAdc})$		, ,	_	2.0	
$(I_C = 8.0 \text{ Adc}, I_B = 80 \text{ mAdc})$			-	2.5	
Base-Emitter On Voltage (I <sub>C</sub> = 8.0 Adc, V <sub>CE</sub> = 4.0 Vdc)		V <sub>BE(on)</sub>	-	2.8	Vdc
DYNAMIC CHARACTERISTICS				•	•
Small-Signal Current Gain (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 4.0 Vdc, f = 1.0 MHz)			4.0	_	_
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	TIP105, TIP106, TIP107	C <sub>ob</sub>	-	300	pF
· /	TIP100, TIP101, TIP102		l _	200	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

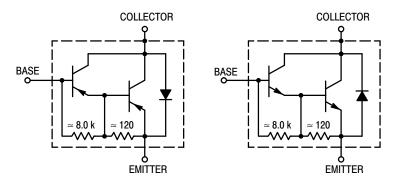


Figure 1. Darlington Circuit Schematic

## **ORDERING INFORMATION**

Device	Package	Shipping
TIP100	TO-220	50 Units / Rail
TIP100G	TO-220 (Pb-Free)	50 Units / Rail
TIP101	TO-220	50 Units / Rail
TIP101G	TO-220 (Pb-Free)	50 Units / Rail
TIP102	TO-220	50 Units / Rail
TIP102G	TO-220 (Pb-Free)	50 Units / Rail
TIP105	TO-220	50 Units / Rail
TIP105G	TO-220 (Pb-Free)	50 Units / Rail
TIP106	TO-220	50 Units / Rail
TIP106G	TO-220 (Pb-Free)	50 Units / Rail
TIP107	TO-220	50 Units / Rail
TIP107G	TO-220 (Pb-Free)	50 Units / Rail

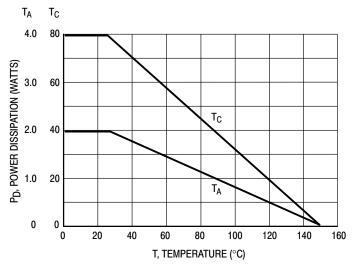


Figure 2. Power Derating

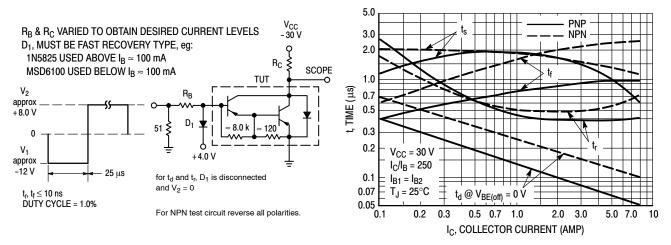


Figure 3. Switching Times Test Circuit

Figure 4. Switching Times

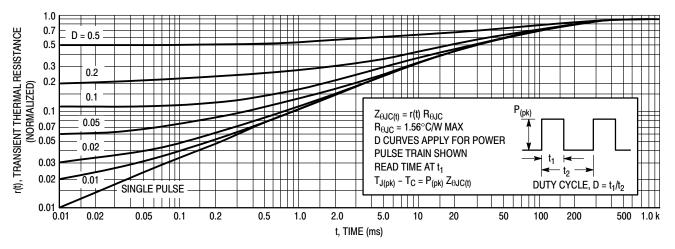


Figure 5. Thermal Response

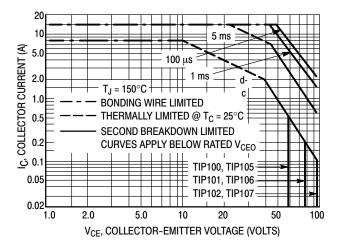


Figure 6. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150$ °C;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)}$  < 150°C.  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown

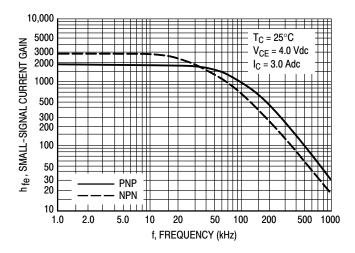


Figure 7. Small-Signal Current Gain

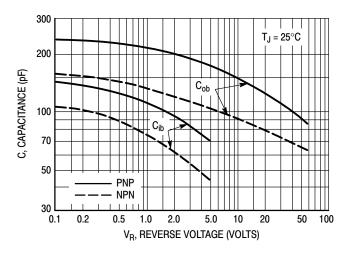


Figure 8. Capacitance

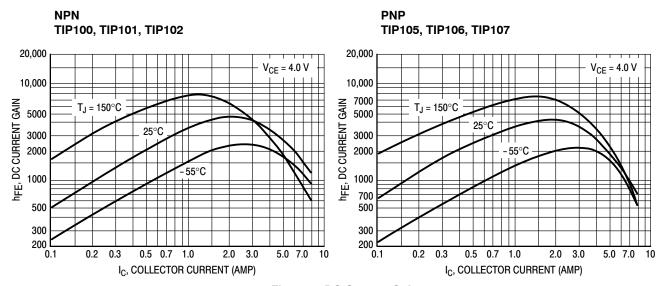


Figure 9. DC Current Gain

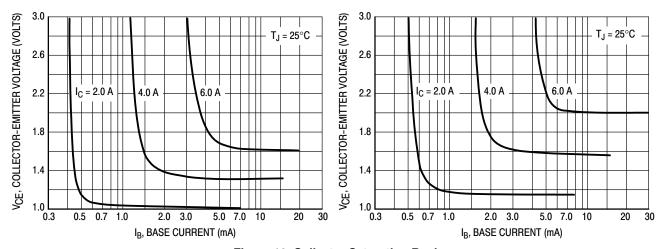


Figure 10. Collector Saturation Region

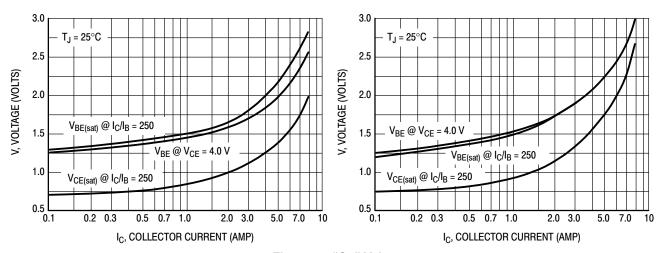
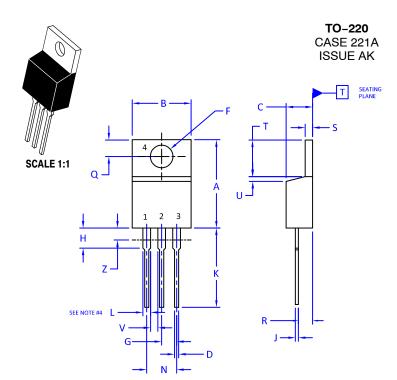


Figure 11. "On" Voltages





**DATE 13 JAN 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	STYLE 6: PIN 1. 2. 3. 4.	CATHODE ANODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.			GATE SOURCE DRAIN SOURCE	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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